

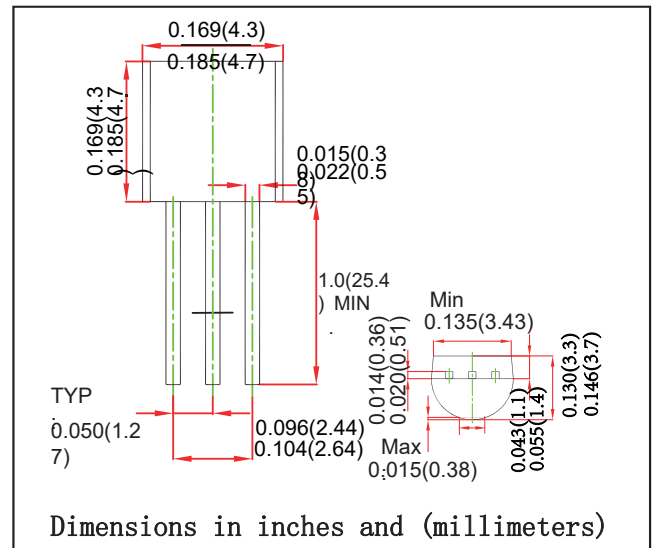
TO-92 Plastic-Encapsulate Transistors

FEATURE

- Excellent h_{FE} Linearity

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.5	A
P_C	Collector Power Dissipation	625	mW
θ_{JA}	Thermal Resistance from Junction to Ambient	200	°C /W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-55~+150	°C

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
S8550	TO-92	Bulk	1000pcs/Bag
S8550-TA	TO-92	Tape	2000pcs/Box

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -50mA$	85		400	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -500mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA, f = 30MHz$	150			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

